16 Mbit (x8/x16) Concurrent SuperFlash

GLS36VF1601E / GLS36VF1602E



Data Sheet

FEATURES:

- Organized as 1M x16 or 2M x8
- Dual Bank Architecture for Concurrent Read/Write Operation
 - 16 Mbit Bottom Sector Protection
 - GLS36VF1601E: 12 Mbit + 4 Mbit
 - 16 Mbit Top Sector Protection
 - GLS36VF1602E: 4 Mbit + 12 Mbit
- Single 2.7-3.6V for Read and Write Operations
- Superior Reliability
 - Endurance: 100,000 cycles (typical)
 - Greater than 100 years Data Retention
- Low Power Consumption:
 - Active Current: 6 mA typical
 - Standby Current: 4 μA typical
 - Auto Low Power Mode: 4 μA typical
- · Hardware Sector Protection/WP# Input Pin
 - Protects the 4 outermost sectors (8 KWord) in the larger bank by driving WP# low and unprotects by driving WP# high
- Hardware Reset Pin (RST#)
 - Resets the internal state machine to reading array data
- Byte# Pin
 - Selects 8-bit or 16-bit mode
- Sector-Erase Capability
 - Uniform 2 KWord sectors
- · Chip-Erase Capability

- Block-Erase Capability
 - Uniform 32 KWord blocks
- Erase-Suspend / Erase-Resume Capabilities
- Security ID Feature
 - Greenliant: 128 bits
 - User: 128 bits
- Fast Read Access Time
 - 70 ns
- Latched Address and Data
- Fast Erase and Program (typical):
 - Sector-Erase Time: 18 ms
 - Block-Erase Time: 18 ms
 - Chip-Erase Time: 35 ms
 - Program Time: 7 μs
- Automatic Write Timing
 - Internal V_{PP} Generation
- End-of-Write Detection
 - Toggle Bit
 - Data# Polling
 - Ready/Busy# pin
- CMOS I/O Compatibility
- · Conforms to Common Flash Memory Interface (CFI)
- JEDEC Standards
 - Flash EEPROM Pinouts and command sets
- · Packages Available
 - 48-ball TFBGA (6mm x 8mm)
 - 48-lead TSOP (12mm x 20mm)

PRODUCT DESCRIPTION

The GLS36VF1601E and GLS36VF1602E are 1M x16 or 2M x8 CMOS Concurrent Read/Write Flash Memory manufactured with Greenliant's proprietary, high performance CMOS SuperFlash memory technology. The split-gate cell design and thick oxide tunneling injector attain better reliability and manufacturability compared with alternate approaches. The devices write (Program or Erase) with a 2.7-3.6V power supply and conform to JEDEC standard pinouts for x8/x16 memories.

Featuring high performance Program, these devices provide a typical Program time of 7 μ sec and use the Toggle Bit, Data# Polling, or RY/BY# to detect the completion of the Program or Erase operation. To protect against inad-

vertent write, the devices have on-chip hardware and Software Data Protection schemes. Designed, manufactured, and tested for a wide spectrum of applications, these devices are offered with a guaranteed endurance of 10,000 cycles. Data retention is rated at greater than 100 years.

These devices are suited for applications that require convenient and economical updating of program, configuration, or data memory. For all system applications, the devices significantly improve performance and reliability, while lowering power consumption. Since for any given voltage range, the SuperFlash technology uses less current to program and has a shorter erase time, the total energy consumed during any Erase or Program operation



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is less than alternative flash technologies. These devices also improve flexibility while lowering the cost for program, data, and configuration storage applications.

SuperFlash technology provides fixed Erase and Program times, independent of the number of Erase/Program cycles that have occurred. Therefore the system software or hardware does not have to be modified or de-rated as is necessary with alternative flash technologies, whose Erase and Program times increase with accumulated Erase/Program cycles.

To meet high-density, surface-mount requirements, these devices are offered in 48-ball TFBGA and 48-lead TSOP packages. See Figures 6 and 7 for pin assignments.

Device Operation

Memory operation functions are initiated using standard microprocessor write sequences. A command is written by asserting WE# low while keeping CE# low. The address bus is latched on the falling edge of WE# or CE#, whichever occurs last. The data bus is latched on the rising edge of WE# or CE#, whichever occurs first.

Auto Low Power Mode

These devices also have the **Auto Lower Power** mode which puts them in a near standby mode within 500 ns after data has been accessed with a valid Read operation. This reduces the I_{DD} active Read current to 4 μA typically. While CE# is low, the devices exit Auto Low Power mode with any address transition or control signal transition used to initiate another Read cycle, with no access time penalty.

Concurrent Read/Write Operation

The dual bank architecture of these devices allows the Concurrent Read/Write operation whereby the user can read from one bank while programming or erasing in the other bank. For example, reading system code in one bank while updating data in the other bank.

TABLE 1: Concurrent Read/Write State

Bank 1	Bank 2
Read	No Operation
Read	Write
Write	Read
Write	No Operation
No Operation	Read
No Operation	Write

Note: For the purposes of this table, write means to perform Blockor Sector-Erase or Program operations as applicable to the appropriate bank.

Read Operation

The Read operation is controlled by CE# and OE#; both have to be low for the system to obtain data from the outputs. CE# is used for device selection. When CE# is high, the chip is deselected and only standby power is consumed. OE# is the output control and is used to gate data from the output pins. The data bus is in a high impedance state when either CE# or OE# is high. Refer to the Read cycle timing diagram for further details (Figure 8).

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Program Operation

These devices are programmed on a word-by-word or byte-by-byte basis depending on the state of the BYTE# pin. Before programming, one must ensure that the sector which is being programmed is fully erased.

The Program operation is accomplished in three steps:

- Software Data Protection is initiated using the three-byte load sequence.
- 2. Address and data are loaded.

During the Program operation, the addresses are latched on the falling edge of either CE# or WE#, whichever occurs last. The data is latched on the rising edge of either CE# or WE#, whichever occurs first.

3. The internal Program operation is initiated after the rising edge of the fourth WE# or CE#, whichever occurs first. The Program operation, once initiated, will be completed typically within 7 µs.

See Figures 9 and 10 for WE# and CE# controlled Program operation timing diagrams and Figure 24 for flow-charts. During the Program operation, the only valid reads are Data# Polling and Toggle Bit. During the internal Program operation, the host is free to perform additional tasks. Any commands issued during an internal Program operation are ignored.

Sector-Erase/Block-Erase Operation

These devices offer both Sector-Erase and Block-Erase operations. These operations allow the system to erase the devices on a sector-by-sector (or block-by-block) basis. The sector architecture is based on a uniform sector size of 2 KWord. The Block-Erase mode is based on a uniform block size of 32 KWord. The Sector-Erase operation is initiated by executing a six-byte command sequence with a Sector-Erase command (30H) and sector address (SA) in the last bus cycle. The Block-Erase operation is initiated by executing a six-byte command sequence with Block-Erase command (50H) and block address (BA) in the last bus cycle. The sector or block address is latched on the falling edge of the sixth WE# pulse, while the command (30H or 50H) is latched on the rising edge of the sixth WE# pulse. The internal Erase operation begins after the sixth WE# pulse. Any commands issued during the Sector- or Block-Erase operation are ignored except Erase-Suspend and Erase-Resume. See Figures 14 and 15 for timing waveforms.

Chip-Erase Operation

The devices provide a Chip-Erase operation, which allows the user to erase all sectors/blocks to the "1" state. This is useful when a device must be quickly erased.

The Chip-Erase operation is initiated by executing a sixbyte command sequence with Chip-Erase command (10H) at address 555H in the last byte sequence. The Erase operation begins with the rising edge of the sixth WE# or CE#, whichever occurs first. During the Erase operation, the only valid Read is Toggle Bit or Data# Polling. Any commands issued during the Chip-Erase operation are ignored. See Table 6 for the command sequence, Figure 13 for timing diagram, and Figure 28 for the flowchart. When WP# is low, any attempt to Chip-Erase will be ignored.



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Erase-Suspend/Erase-Resume Operations

The Erase-Suspend operation temporarily suspends a Sector- or Block-Erase operation thus allowing data to be read from any memory location, or program data into any sector/block that is not suspended for an Erase operation. The operation is executed by issuing a one-byte command sequence with Erase-Suspend command (B0H). The device automatically enters read mode no more than 10 µs after the Erase-Suspend command had been issued. (TES maximum latency equals 10 µs.) Valid data can be read from any sector or block that is not suspended from an Erase operation. Reading at address location within erasesuspended sectors/blocks will output DQ2 toggling and DQ6 at "1". While in Erase-Suspend mode, a Program operation is allowed except for the sector or block selected for Erase-Suspend. To resume Sector-Erase or Block-Erase operation which has been suspended, the system must issue an Erase-Resume command. The operation is executed by issuing a one-byte command sequence with Erase Resume command (30H) at any address in the onebyte sequence.

Write Operation Status Detection

These devices provide one hardware and two software means to detect the completion of a Write (Program or Erase) cycle in order to optimize the system Write cycle time. The hardware detection uses the Ready/Busy# (RY/BY#) output pin. The software detection includes two status bits: Data# Polling (DQ $_7$) and Toggle Bit (DQ $_6$). The End-of-Write detection mode is enabled after the rising edge of WE#, which initiates the internal Program or Erase operation.

The actual completion of the nonvolatile write is asynchronous with the system; therefore, either a Ready/Busy# (RY/BY#), a Data# Polling (DQ $_7$), or Toggle Bit (DQ $_6$) Read may be simultaneous with the completion of the Write cycle. If this occurs, the system may get an erroneous result, i.e., valid data may appear to conflict with either DQ $_7$ or DQ $_6$. In order to prevent spurious rejection if an erroneous result occurs, the software routine should include a loop to read the accessed location an additional two (2) times. If both Reads are valid, then the Write cycle has completed, otherwise the rejection is valid.

Ready/Busy# (RY/BY#)

The devices include a Ready/Busy# (RY/BY#) output signal. RY/BY# is an open drain output pin that indicates whether an Erase or Program operation is in progress. Since RY/BY# is an open drain output, it allows several devices to be tied in parallel to V_{DD} via an external pull-up resistor. After the rising edge of the final WE# pulse in the command sequence, the RY/BY# status is valid.

When RY/BY# is actively pulled low, it indicates that an Erase or Program operation is in progress. When RY/BY# is high (Ready), the devices may be read or left in standby mode.

Byte/Word (BYTE#)

The device includes a BYTE# pin to control whether the device data I/O pins operate x8 or x16. If the BYTE# pin is at logic "1" (V_{IH}) the device is in x16 data configuration: all data I/O pins DQ₀-DQ₁₅ are active and controlled by CE# and OE#.

If the BYTE# pin is at logic "0", the device is in x8 data configuration: only data I/O pins DQ_0 - DQ_7 are active and controlled by CE# and OE#. The remaining data pins DQ_8 - DQ_{14} are at Hi-Z, while pin DQ_{15} is used as the address input A_{-1} for the Least Significant Bit of the address bus.

Data# Polling (DQ₇)

When the devices are in an internal Program operation, any attempt to read DQ_7 will produce the complement of the true data. Once the Program operation is completed, DQ_7 will produce true data. During internal Erase operation, any attempt to read DQ_7 will produce a '0'. Once the internal Erase operation is completed, DQ_7 will produce a '1'. The Data# Polling is valid after the rising edge of fourth WE# (or CE#) pulse for Program operation. For Sector-, Block-, or Chip-Erase, the Data# Polling is valid after the rising edge of sixth WE# (or CE#) pulse. See Figure 11 for Data# Polling (DQ_7) timing diagram and Figure 25 for a flowchart.

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Toggle Bits (DQ₆ and DQ₂)

During the internal Program or Erase operation, any consecutive attempts to read DQ_6 will produce alternating "1"s and "0"s, i.e., toggling between 1 and 0. When the internal Program or Erase operation is completed, the DQ_6 bit will stop toggling. The device is then ready for the next operation. The toggle bit is valid after the rising edge of the fourth WE# (or CE#) pulse for Program operations. For Sector-, Block-, or Chip-Erase, the toggle bit (DQ_6) is valid after the rising edge of sixth WE# (or CE#) pulse. DQ_6 will be set to "1" if a Read operation is attempted on an Erase-suspended Sector/Block. If Program operation is initiated in a sector/block not selected in Erase-Suspend mode, DQ_6 will toggle.

An additional Toggle Bit is available on DQ_2 , which can be used in conjunction with DQ_6 to check whether a particular sector is being actively erased or erase-suspended. Table 2 shows detailed status bit information. The Toggle Bit (DQ_2) is valid after the rising edge of the last WE# (or CE#) pulse of a Write operation. See Figure 12 for Toggle Bit timing diagram and Figure 25 for a flowchart.

TABLE 2: Write Operation Status

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Status		DQ ₇	DQ_6	DQ_2	RY/BY#
Normal Operation	Standard Program	DQ7#	Toggle	No Toggle	0
	Standard Erase	0	Toggle	Toggle	0
Erase- Suspend Mode	Read From Erase Suspended Sector/Block	1	1	Toggle	1
	Read From Non-Erase Suspended Sector/Block	Data	Data	Data	1
	Program	DQ7#	Toggle	N/A	0

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Note: DQ_7 , DQ_6 , and DQ_2 require a valid address when reading status information. The address must be in the bank where the operation is in progress in order to read the operation status. If the address is pointing to a different bank (not busy), the device will output array data.

Data Protection

The devices provide both hardware and software features to protect nonvolatile data from inadvertent writes.

Hardware Data Protection

Noise/Glitch Protection: A WE# or CE# pulse of less than 5 ns will not initiate a Write cycle.

 V_{DD} Power Up/Down Detection: The Write operation is inhibited when V_{DD} is less than 1.5V.

<u>Write Inhibit Mode:</u> Forcing OE# low, CE# high, or WE# high will inhibit the Write operation. This prevents inadvertent writes during power-up or power-down.

Hardware Block Protection

The devices provide hardware block protection which protects the outermost 8 KWord in the larger bank. The block is protected when WP# is held low. See Figures 2, 3, 4, and 5 for Block-Protection location.

A user can disable block protection by driving WP# high. This allows data to be erased or programmed into the protected sectors. WP# must be held high prior to issuing the Write command and remain stable until after the entire Write operation has completed. If WP# is left floating, it is internally held high via a pull-up resistor, and the Boot Block is unprotected, enabling Program and Erase operations on that block.

Hardware Reset (RST#)

The RST# pin provides a hardware method of resetting the devices to read array data. When the RST# pin is held low for at least T_{RP} , any in-progress operation will terminate and return to Read mode (see Figure 21). When no internal Program/Erase operation is in progress, a minimum period of T_{RHR} is required after RST# is driven high before a valid Read can take place (see Figure 20).

The Erase operation that has been interrupted needs to be reinitiated after the device resumes normal operation mode to ensure data integrity.



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Software Data Protection (SDP)

These devices provide the JEDEC standard Software Data Protection scheme for all data alteration operations, i.e., Program and Erase. Any Program operation requires the inclusion of the three-byte sequence. The three-byte load sequence is used to initiate the Program operation, providing optimal protection from inadvertent Write operations, e.g., during the system power-up or power-down. Any Erase operation requires the inclusion of the six-byte sequence. The devices are shipped with the Software Data Protection permanently enabled. See Table 6 for the specific software command codes. During SDP command sequence, invalid commands will abort the device to Read mode within $T_{\rm RC}$. The contents of $DQ_{15}\text{-}DQ_{8}$ can be $V_{\rm IL}$ or $V_{\rm IH}$, but no other value during any SDP command sequence.

Common Flash Memory Interface (CFI)

These devices also contain the CFI information to describe the characteristics of the devices. In order to enter the CFI Query mode, the system must write the three-byte sequence, same as the Software ID Entry command with 98H (CFI Query command) to address 555H in the last byte sequence. See Figure 17 for CFI Entry and Read timing diagram. Once the device enters the CFI Query mode, the system can read CFI data at the addresses given in Tables 7 through 9. The system must write the CFI Exit command to return to Read mode from the CFI Query mode.

Security ID

The GLS36VF160xE devices offer a 256-bit Security ID space. The Secure ID space is divided into two 128-bit segments—one factory programmed segment and one user programmed segment. The first segment is programmed and locked at Greenliant with a unique, 128-bit number. The user segment is left un-programmed for the customer to program as desired. To program the user segment of the Security ID, the user must use the Security ID Program command. End-of-Write status is checked by reading the toggle bits. Data# Polling is not used for Security ID End-of-Write detection. Once programming is complete, the Sec ID should be locked using the User Sec ID Program Lock-Out. This disables any future corruption of this space. Note that regardless of whether or not the Sec ID is locked, neither Sec ID segment can be erased. The Secure ID space can be queried by executing a three-byte command sequence with Query Sec ID command (88H) at address 555H in the last byte sequence. See Figure 19 for timing diagram. To exit this mode, the Exit Sec ID command should be executed. Refer to Table 6 for more details.

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Product Identification

The Product Identification mode identifies the devices and manufacturer. For details, see Table 3 for software operation, Figure 16 for the Software ID Entry and Read timing diagram and Figure 26 for the Software ID Entry command sequence flowchart. The addresses A_{19} and A_{18} indicate a bank address. When the addressed bank is switched to Product Identification mode, it is possible to read another address from the same bank without issuing a new Software ID Entry command.

TABLE 3: Product Identification

	Address	Data
Manufacturer's ID	BK0000H	00BFH
Device ID		
GLS36VF1601E	BK0001H	734BH
GLS36VF1602E	BK0001H	734AH

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Note: BK = Bank Address (A₁₉-A₁₈)

Product Identification Mode Exit/CFI Mode Exit

In order to return to the standard Read mode, the Software Product Identification mode must be exited. Exit is accomplished by issuing the Software ID Exit command sequence, which returns the device to the Read mode. This command may also be used to reset the device to the Read mode after any inadvertent transient condition that apparently causes the device to behave abnormally, e.g., not read correctly. Please note that the Software ID Exit/CFI Exit command is ignored during an internal Program or Erase operation. See Table 6 for the software command code, Figure 18 for timing waveform and Figure 27 for a flowchart.

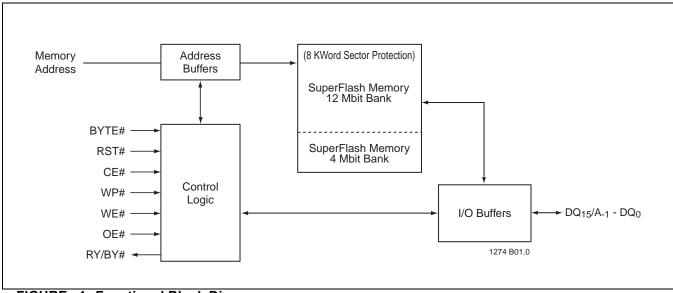


FIGURE 1: Functional Block Diagram



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Bottom Sector Protection; 32 KWord Blocks; 2 KWord Sectors

	Dioak 24	FFFFFH
	Block 31	F8000H
	Block 30	F7FFFH F0000H
i	B	EFFFFH
	Block 29	E8000H
Bank 2	Block 28	E7FFFH
ᆝ긎		E0000H DFFFFH
l N	Block 27	D8000H
1	Block 26	D7FFFH
	DIOCK 20	D0000H CFFFH
	Block 25	C8000H
1	Block 24	C7FFFH
	DIOCK 24	C0000H
	Block 23	BFFFFH
ł		B8000H B7FFFH
	Block 22	B0000H
1	Dia als 04	AFFFH
	Block 21	A8000H
	Block 20	A7FFFH
		A0000H 9FFFFH
	Block 19	98000H
1	Block 18	97FFFH
	DIOCK TO	90000H
	Block 17	8FFFFH 88000H
1		87FFFH
	Block 16	80000H
	Block 15	7FFFFH
-	Diook 10	78000H
	Block 14	77FFFH 70000H
1	Dis als 40	6FFFFH
	Block 13	68000H
\Box	Block 12	67FFFH
Bank		60000H 5FFFFH
웃	Block 11	58000H
	Block 10	57FFFH
	Blook 10	50000H
	Block 9	4FFFFH 48000H
1	Di. i o	47FFFH
	Block 8	40000H
	Block 7	3FFFFH
-		38000H 37FFFH
	Block 6	30000H
1	Block 5	2FFFFH
	DIOCK 3	28000H
	Block 4	27FFFH 20000H
1	DI. I O	1FFFFH
	Block 3	18000H
	Block 2	17FFFH
-		10000H 0FFFFH
	Block 1	08000H
1		07FFFH
	Block 0	02000H
		01FFFH
		00000H

8 KWord Sector Protection Sectors) (4-2 KWord Sectors)

Note: The address input range in x16 mode (BYTE#= V_{IH}) is A_{19} - A_{0}

FIGURE 2: GLS36VF1601E, 1M x16 Concurrent SuperFlash Dual-Bank Memory Organization



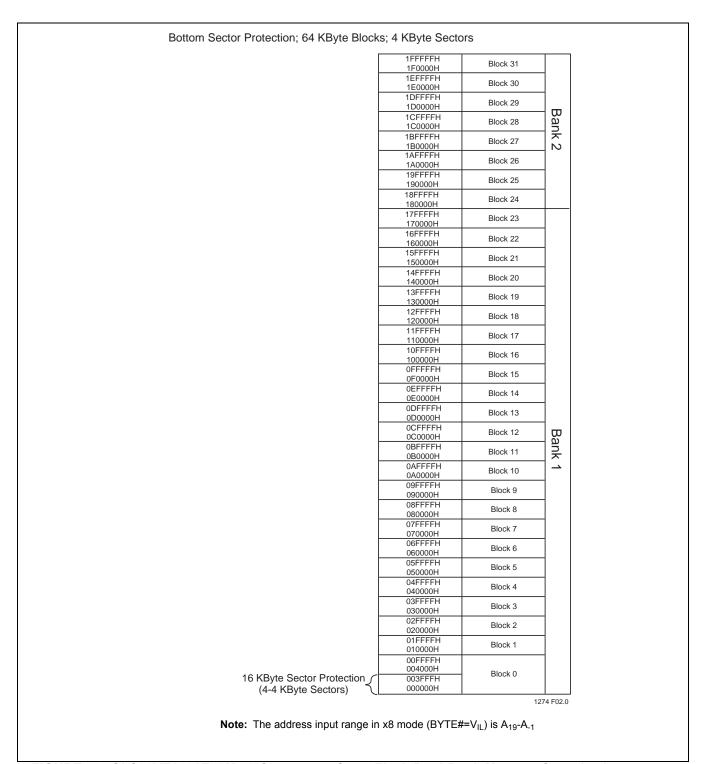


FIGURE 3: GLS36VF1601E, 2M x8 Concurrent SuperFlash Dual-Bank Memory Organization



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Top Block Protection; 32 KWord Blocks; 2 KWord Sectors

8 KWord Block Protection (4 - 2 KWord Sectors)

FFFFFH FE000H FDFFFH	Block 31	
F8000H F7FFFH	District 20	-
F0000H EFFFFH	Block 30	-
E8000H	Block 29	-
E7FFFH E0000H	Block 28	
DFFFFH D8000H	Block 27	
D7FFFH	Block 26	
D0000H CFFFFH	Block 25	1
C8000H C7FFFH		-
C0000H	Block 24	_
BFFFFH B8000H	Block 23	
B7FFFH B0000H	Block 22	
AFFFFH	Block 21	B
A8000H A7FFFH	Block 20	Bank
A0000H 9FFFFH		
98000H	Block 19	-
97FFFH 90000H	Block 18	
8FFFFH 88000H	Block 17	
87FFFH	Block 16	
80000H 7FFFFH	Block 15	-
78000H 77FFFH	Block 14	-
70000H 6FFFFH		_
68000H	Block 13	-
67FFFH 60000H	Block 12	
5FFFFH 58000H	Block 11	
57FFFH	Block 10	
50000H 4FFFH	Block 9	1
48000H 47FFFH		-
40000H 3FFFFH	Block 8	<u> </u>
38000H	Block 7	
37FFFH 30000H	Block 6	
2FFFH 28000H	Block 5	_
27FFFH	Block 4	Ba
20000H 1FFFFH	Block 3	궂
18000H 17FFFH		_
10000H 0FFFFH	Block 2	-
H00080	Block 1	
07FFFH 00000H	Block 0	
	12	74 F03.0

1274 F03.0

Note: The address input range in x16 mode (BYTE#=VIH) is

FIGURE 4: GLS36VF1602E, 1M x16 Concurrent SuperFlash Dual-Bank Memory Organization



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Top Block Protection; 64 KByte Blocks; 4 KByte Sectors

16 KByte Block Protection (4 - 4 KByte Sectors)

1FC000H			
1FBFFFH	1FFFFFH		
TFBFFFH 1F0000H 1FFFFH 1F0000H 1FFFFH 1E0000H 1E00000H 1E000000H 1		Block 31	
TEFFFFH 1E0000H Block 30 1DFFFFH 1E0000H Block 29 1CFFFFH 1D0000H Block 28 1EFFFFH 1D0000H Block 27 1AFFFFH 1B0000H Block 26 19FFFFH 190000H Block 25 18FFFFH 190000H Block 24 17FFFFH Block 23 16FFFFH 170000H Block 21 12FFFFH 150000H Block 21 12FFFFH 150000H Block 21 13FFFFH 130000H Block 19 12FFFFH 120000H Block 18 11FFFFH 120000H Block 16 10FFFFH 100000H Block 16 10FFFFFH 100000H Block 15 10FFFFH 10E0000H Block 14 10EFFFFH 10E0000H Block 13 10FFFFH 10E0000H Block 14 10EFFFFH 10E0000H Block 10 10FFFFH 10E0000H Block 11 10EFFFFH 10E0000H Block 11 10EFFFFH 10E0000H Block 10 10EFFFFH 10E0000H Block 10 10EFFFFH 10E0000H Block 10 10EFFFFH 10EO000H Block 5 10EEFFFFH 10EO000H Block 5 10EEFFFFH 10EO000H Block 5 10EEFFFFH 10EO000H Block 5 10EEFFFFH 10EO000H Block 5 10EEFFFH 10EO000H 10EEFFFH 10EE			
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1D0000H Block 29			l
100000H 10FFFFH 1C0000H 11FFFFH 1C0000H 11FFFFH 1B0000H 11FFFFH 1B0000H 11FFFFH 1B0000H 11FFFFH 170000H 11FFFFH 170000H 11FFFFH 150000H 11FFFFH 150000H 11FFFFH 130000H 11FFFFH 130000H 11FFFFH 130000H 11FFFFH 130000H 11FFFFH 130000H 11FFFFH 10000H 10FFFFH 10000H 10FFFFH 10000H 10FFFFH 10000H 10FFFFH 10000H 10FFFFH 10F000H 10FFFFH 10FFFH 10FFF		Block 29	
1C0000H Block 28 1BFFFFH 1B0000H Block 26 1AFFFFH 1A0000H Block 25 18FFFFH 199000H Block 24 18FFFFH 199000H Block 24 18FFFFH 180000H Block 23 16FFFFH Block 22 15FFFFH Block 21 150000H Block 21 15FFFFH Block 20 13FFFFH Block 19 13FFFFH Block 19 12FFFFH Block 17 10FFFFH Block 16 10FFFFH Block 17 10FFFFH Block 15 0FFFFFH Block 14 0F0000H Block 15 0FFFFFH Block 12 0FFFFH Block 13 0FFFFH Block 14 0FFFFH Block 10 0FFFFFH Block 10 0FFFFFH Block 10 0FFFFFH Block 8 07FFFFH Block 8 07FFFFH 080000H Block 7 06FFFFH 080000H Block 6 05FFFFH 080000H Block 5 06FFFFH Block 5 050000H Block 5 04FFFFH Block 5 050000H Block 5 04FFFFH Block 5 050000H Block 5 04FFFFH Block 5 050000H Block 5 05000H Block 5 050000H Block 5 05000H 05000H Block 5 05000H Block 5 05000H 05000H 05000H Block 5 05000H		Dioon 20	
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180000H 1810ck 27 187FFFH 180000H 1810ck 25 18FFFFH 180000H 1810ck 24 18FFFFH 180000H 1810ck 23 18FFFFH 180000H 1810ck 22 16FFFFH 180000H 1810ck 21 18FFFFH 180000H 1810ck 21 18FFFFH 180000H 1810ck 19 1810ck 19 1810ck 19 1810ck 19 1810ck 18 1810ck 18 1810ck 18 1810ck 18 1810ck 16			l
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1A0000H 19FFFFH 19000H 19FFFFH 190000H 18FFFFH 180000H 17FFFFH 170000H 18FFFFH 180000H 18Bock 18 18FFFH 180000H 18Bock 18 18FFFH 18Bock 18 18FFFFH 18Bock 18 18		Block 26	
19000H 18FFFFH 180000H 17FFFFH 170000H 16FFFFH 180000H 15FFFFH 180000H 15FFFFH 180000H 14FFFFH 180000H 14FFFFH 180000H 14FFFFH 180000H 13FFFFH 180000H 12FFFFH 120000H 12FFFFH 120000H 16FFFFH 100000H 16FFFFH 100000H 17FFFFH 100000H 18 lock 16 18 lock 17 19 lock 16 19 lock 16 10 lock 17 10 lock 18 11 lock 16 10 lock 16 10 lock 16 10 lock 17 10 lock 18 10 lock 18 11 lock 16 10 lock 16 10 lock 16 10 lock 17 10 lock 18 10 lock 19 10 lock 10 10 lock 11 10 lock 10			
190000H 18FFFFH 18000H 18FFFFH 180000H 17FFFFH 160000H 16FFFFH 160000H 16FFFFH 150000H 16FFFFH 140000H 16FFFFH 130000H 12FFFFH 130000H 12FFFFH 120000H 12FFFFH 110000H 16FFFFH 100000H 16FFFFH 100000H 16FFFFH 100000H 16FFFFH 16FFFH 16FFFFH 16FFFFFH 16FFFFH 16FFFFFH 16FFFFH 16FFFH 16FFFFH 16FFFH 16FFFFH 16FFFH 16FFFFH 16FFFH 16FFFFH 16FFFFH 16FFFH 16FFFFH 16FFFH 1	-	Block 25	
180000H Block 24	190000H	5.00K 20	
180000H	18FFFFH	Block 24	
170000H Block 23	180000H	DIOCK 24	
170000H 16FFFFH 160000H 16FFFFH 150000H 15FFFFH 150000H 14FFFFH 140000H 13FFFFH 130000H 12FFFFH 120000H 11FFFFH 110000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 10FFFH 1	17FFFFH	Block 23	
160000H Block 22 15FFFFH 150000H Block 21 14FFFFH 140000H Block 19 12FFFFH 130000H Block 18 12FFFFH 120000H Block 17 100000H Block 16 100000H Block 15 100000H Block 15 100000H Block 15 100000H Block 14 100000H Block 14 100000H Block 13 100000H Block 12 100000H Block 12 100000H Block 11 100000H Block 10 100000H 100	170000H	DIOCK 23	
150000H 15000H 15000H 150000H 150000H 150000H 14FFFH 150000H 14FFFFH 130000H 13FFFFH 130000H 12FFFFH 120000H 11FFFFH 110000H 11FFFFH 100000H 10FFFFH 100000H	16FFFFH	Block 22	
150000H Block 21 20 20 20 20 20 20 20	160000H	DIOUN ZZ	1
130000H 12FFFFH 120000H 12FFFFH 120000H 11FFFFH 110000H 11FFFFH 110000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 10E0000H 10EFFFH 10E0000H 10EFFFFH 10E0000H 10EFFFFH 10EFFFH 10	15FFFFH	Block 24	
130000H 12FFFFH 120000H 12FFFFH 120000H 11FFFFH 110000H 11FFFFH 110000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 10E0000H 10EFFFH 10E0000H 10EFFFFH 10E0000H 10EFFFFH 10EFFFH 10	150000H	DIUUK Z I	lω
130000H 12FFFFH 120000H 12FFFFH 120000H 11FFFFH 110000H 11FFFFH 110000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 10E0000H 10EFFFH 10E0000H 10EFFFFH 10E0000H 10EFFFFH 10EFFFH 10	14FFFFH	Plack 20	15
130000H 12FFFFH 120000H 12FFFFH 120000H 11FFFFH 110000H 11FFFFH 110000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 100000H 10FFFFH 10E0000H 10EFFFH 10E0000H 10EFFFFH 10E0000H 10EFFFFH 10EFFFH 10	140000H	BIOCK 20	
130000H 12FFFFH 120000H 11FFFFH 110000H 11FFFFH 110000H 10FFFFH 100000H 0FFFFFH 0F0000H 0DFFFFH 0D0000H 0DFFFFH 0B0000H 0BFFFFH 0B0000H 0AFFFFH 0B0000H 0BFFFFH 0B0000H 0B000H 0B00	13FFFFH	Disale 40	N
12FFFFH 120000H 11FFFFH 110000H 11FFFFH 110000H 10FFFFH 100000H 0FFFFFH 0F0000H 0FFFFFH 0F0000H 0FFFFH 0FFFH 0F	130000H	DIOCK 19	
120000H 11FFFFH 110000H 10FFFFH 110000H 10FFFFH 100000H 0FFFFFH 0F0000H 0EFFFFH 0E0000H 0DFFFFH 0D0000H 0DFFFFH 0D0000H 0DFFFFH 0D0000H 0DFFFFH 0E0000H 0BFFFFH 0B0000H 0AFFFFH 0B0000H 0AFFFFH 0B0000H 0FFFFH 0B0000H		Plook 19	
11FFFFH 110000H Block 17 10FFFFH 100000H DFFFFFH DF0000H DEFFFFH DE0000H DFFFFFH DE0000H DFFFFH DF0000H DF00000H DF000000H DF00000H DF000000H DF000000H DF000000H DF000000H DF000000H DF0000000H DF000000	120000H	DIUCK 10]
110000H		Diagle 47	1
100000H Block 15	110000H	DIOCK 17	
100000H	10FFFFH	Plook 16	
OF0000H Block 15 0EFFFFH Block 14 0E0000H Block 14 0D0FFFFH Block 13 0CFFFFH Block 12 0C0000H Block 12 0BFFFH Block 11 0AFFFH Block 10 09FFFH Block 9 090000H Block 8 07FFFH Block 8 07FFFFH Block 7 06FFFFH Block 6 05FFFFH Block 5 050000H Block 5 04FFFFH Block 5	100000H	DIOCK TO	
OF-0000H	0FFFFFH	Plook 15	
OE0000H Block 14 ODFFFFH DD0000H OCFFFFH Block 13 OCFFFFH Block 12 OBFFFFH Block 11 OB0000H Block 10 O3FFFFH Block 9 O30000H Block 9 O8FFFFH Block 8 O7FFFFH Block 7 O6FFFFH Block 6 O5FFFFH Block 6 O5FFFFH Block 5 O50000H D4FFFFH Block 4 D	0F0000H	DIUCK 13]
OE0000H	0EFFFFH	Block 14	
OD0000H Block 13	0E0000H	DIUCK 14	
D00000H D10ck 12 D10ck 12 D10ck 12 D10ck 14 D10ck 15 D10ck 16	0DFFFFH	Plook 12	
OC0000H Block 12 0BFFFFH Block 11 0B0000H Block 11 0AFFFFH Block 10 09FFFFH Block 9 090000H Block 8 07FFFFH Block 7 070000H Block 7 06FFFFH 060000H 05FFFFH Block 5 050000H Block 5 04FFFFH Block 4	0D0000H	DIUCK 13]
0C0000H 0BFFFFH 0B0000H 0AFFFFH 0A0000H 09FFFFH 090000H 08FFFFH 080000H 07FFFFH 0770000H 06FFFFH 060000H 05FFFFH 050000H 05FFFFH 050000H 04FFFFH DS0000H 04FFFFH DS0000H DD0000H DD00000H DD0000H DD	0CFFFFH	Plook 12	
0B0000H Block 10 0AFFFFH 0A0000H 09FFFFH Block 9 090000H Block 8 08FFFFH Block 8 080000H Block 7 07000H Block 7 06FFFFH Block 6 05FFFFH Block 5 050000H Block 5 050000H Block 4	0C0000H	DIUCK 12	
0B0000H 0AFFFFH 0A000H 0SFFFFH 090000H 08FFFFH 080000H 07FFFFH 070000H 06FFFFH 060000H 05FFFFH 050000H 04FFFFH DS0000H 04FFFFH DS0000H 04FFFFH DS0000H DBlock 5 DBlock 5 DBlock 5 DBlock 4 DD	0BFFFFH	Plook 11	
0AFFFFH 0A0000H Block 10 09FFFFH 090000H Block 9 08FFFFH 080000H Block 8 07FFFFH 070000H Block 7 06FFFFH 060000H Block 6 05FFFFH 050000H Block 5 04FFFFH Block 4		DIUUK I I	1
0A0000H 09FFFFH 090000H 08FFFFH 080000H 07FFFFH 0770000H 06FFFFH 060000H 05FFFFH 050000H 04FFFFH D50000H D4FFFFH D80044		Block 10	
09FFFFH 090000H Block 9 08FFFFH 080000H Block 8 07FFFFH 070000H Block 7 06FFFFH 060000H Block 6 05FFFFH 050000H Block 5 04FFFFH Block 4	0A0000H	DIUUK 10	
090000H 08FFFFH 080000H 07FFFFH 070000H 06FFFFH 060000H 05FFFFH 050000H 04FFFFH Block 5 09000H 04FFFFH Block 4		Block 9	l
08FFFFH 080000H Block 8 07FFFFH 070000H Block 7 06FFFFH 060000H Block 6 05FFFFH 050000H Block 5 04FFFFH Block 4	090000H	DIOCK 9	
080000H 07FFFFH 070000H 06FFFFH 080000H 05FFFFH 050000H 04FFFFH DBlock 5 04FFFFH DBlock 4		Block 9	
07FFFFH 070000H Block 7 06FFFFH 060000H Block 6 05FFFFH 050000H Block 5 04FFFFH Block 4	080000H	DIUUK O	
070000H Block 7 06FFFFH 060000H 05FFFFH 050000H 04FFFFH Block 5 04FFFFH Block 4		Block 7	
060000H 05FFFFH 050000H 04FFFFH Black 4 0		DIOCK /	
060000H 05FFFFH 050000H 04FFFFH Black 4 0		Block 6	
05FFFFH Block 5 050000H UU 04FFFFH Block 4		DIUCK 0	
050000H	05FFFFH	Plook E	1
I Block 4 I 🖼	050000H	DIOCK 3	l
0.4000011 DIUCK 4 =	04FFFFH	Plook 4	186
U4UUU0H 3	040000H	DIUUK 4] 5
00EEEE11 7		Block 2	
030000H Block 3		DIUCK 3	
0255551		District O	1
020000H Block 2		DIUCK Z	
0155554		Block 1]
010000H Block 1	010000H	DIUCK I	
00FFFFH Block 0		Block 0]
000000H		DIOCK 0	
1274 F04.		1274	F04.0

Note: The address input range in x8 mode (BYTE#= V_{IL}) is

FIGURE 5: GLS36VF1602E, 2M x8 Concurrent SuperFlash Dual-Bank Memory Organization



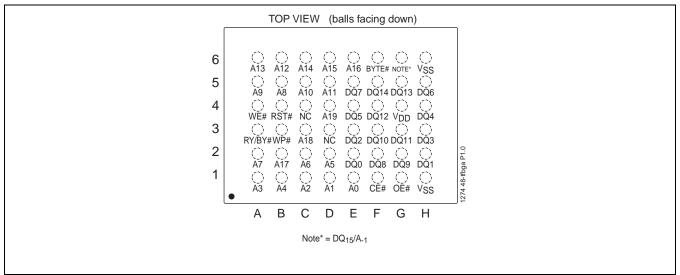


FIGURE 6: Pin Assignments for 48-ball TFBGA (6mm x 8mm)

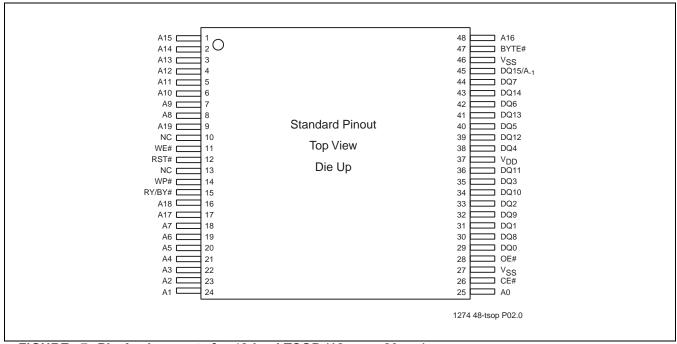


FIGURE 7: Pin Assignments for 48-lead TSOP (12mm x 20mm)



Data Sheet

TABLE 4: Pin Description

Symbol	Name	Functions
A ₁₉ -A ₀	Address Inputs	To provide memory addresses. During Sector-Erase and Hardware Sector Protection, A_{19} - A_{11} address lines will select the sector. During Block-Erase A_{19} - A_{15} address lines will select the block.
DQ ₁₄ -DQ ₀	Data Input/Output	To output data during Read cycles and receive input data during Write cycles Data is internally latched during a Write cycle. The outputs are in tri-state when OE# or CE# is high.
DQ ₁₅ /A ₋₁	Data Input/Output and LBS Address	DQ_{15} is used as data I/O pin when in x16 mode (BYTE# = "1") A ₋₁ is used as the LSB address pin when in x8 mode (BYTE# = "0")
CE#	Chip Enable	To activate the device when CE# is low.
OE#	Output Enable	To gate the data output buffers
WE#	Write Enable	To control the Write operations
RST#	Hardware Reset	To reset and return the device to Read mode
RY/BY#	Ready/Busy#	To output the status of a Program or Erase operation RY/BY# is a open drain output, so a $10K\Omega$ - $100K\Omega$ pull-up resistor is required to allow RY/BY# to transition high indicating the device is ready to read.
WP#	Write Protect	To protect and unprotect top or bottom 8 KWord (4 outermost sectors) from Erase or Program operation.
BYTE#	Word/Byte Configuration	To select 8-bit or 16-bit mode.
V_{DD}	Power Supply	To provide 2.7-3.6V power supply voltage
V_{SS}	Ground	
NC	No Connection	Unconnected pins

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TABLE 5: Operation Modes Selection

					DQ ₁₅ -DQ ₈		
Mode ¹	CE#	OE#	WE#	DQ_7 - DQ_0	BYTE# = V _{IH}	BYTE# = V _{IL}	Address
Read	V _{IL}	V _{IL}	V _{IH}	D _{OUT}	D _{OUT}	DQ_{14} - DQ_{8} = High Z	A _{IN}
Program	V_{IL}	V_{IH}	V_{IL}	D _{IN}	D _{IN}	$DQ_{15} = A_{-1}$	A _{IN}
Erase	V _{IL}	V _{IH}	V _{IL}	X ²	Х	High Z	Sector or Block address, 555H for Chip-Erase
Standby	V_{IHC}	Х	Х	High Z	High Z	High Z	Х
Write Inhibit	Х	V_{IL}	Х	High Z / D _{OUT}	High Z / D _{OUT}	High Z	Х
	Х	Х	V _{IH}	High Z / D _{OUT}	High Z / D _{OUT}	High Z	Х
Product Identification							
Software Mode	V _{IL}	V _{IL}	V _{IH}	Manufacturer's ID (BFH)	Manufacturer's ID (00H)	High Z	See Table 6
				Device ID ³	Device ID ³	High Z	

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^{1.} RST# = V_{IH} for all described operation modes

^{2.} X can be V_{IL} or V_{IH} , but no other value.

^{3.} Device ID = GLS36VF1601E = 734BH, GLS36VF1602E = 734AH



Data Sheet

TABLE 6: Software Command Sequence

Command Sequence	1st I Write		2nd Write			Bus Cycle		Bus Cycle	5th Write	Bus Cycle		Bus Cycle
	Addr ¹	Data ²	Addr ¹	Data ²	Addr ¹	Data ²	Addr ¹	Data ²	Addr ¹	Data ²	Addr ¹	Data ²
Program	555H	AAH	2AAH	55H	555H	A0H	WA ³	Data				
Sector-Erase	555H	AAH	2AAH	55H	555H	80H	555H	AAH	2AAH	55H	SA _X ⁴	30H
Block-Erase	555H	AAH	2AAH	55H	555H	80H	555H	AAH	2AAH	55H	BA _X ⁴	50H
Chip-Erase	555H	AAH	2AAH	55H	555H	80H	555H	AAH	2AAH	55H	555H	10H
Erase-Suspend	XXXXH	ВОН										
Erase-Resume	XXXXH	30H										
Query Sec ID ⁵	555H	AAH	2AAH	55H	555H	88H						
User Security ID Program	555H	AAH	2AAH	55H	555H	A5H	SIWA ⁶	Data				
User Security ID Program Lock-out ⁷	555H	AAH	2AAH	55H	555H	85H	XXH	0000H				
Software ID Entry ⁸	555H	AAH	2AAH	55H	BK _X ⁹ 555H	90H						
CFI Query Entry	555H	AAH	2AAH	55H	BK _X ⁹ 555H	98H						
Software ID Exit/ CFI Exit/ Sec ID Exit ^{10,11}	555H	AAH	2AAH	55H	555H	F0H						
Software ID Exit/ CFI Exit/ Sec ID Exit ^{10,11}	XXH	F0H										

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- 1. Address format A₁₀-A₀ (Hex), Addresses A₁₉-A₁₁ can be V_{IL} or V_{IH}, but no other value, for the command sequence when in x16 mode. When in x8 mode, Addresses A₁₉-A₁₂, Address A₋₁ and DQ₁₄-DQ₈ can be V_{IL} or V_{IH}, but no other value, for the command sequence.
- 2. DQ₁₅-DQ₈ can be V_{IL} or V_{IH}, but no other value, for the command sequence
- 3. WA = Program word/byte address
- 4. SA_X for Sector-Erase; uses A₁₉-A₁₁ address lines BA_X for Block-Erase; uses A₁₉-A₁₅ address lines
- For GLS36VF1601E,

Greenliant ID is read with $A_3 = 0$ (Address range = 00000H to 00007H).

User ID is read with $A_3 = 1$ (Address range = 00010H to 00017H).

Lock Status is read with A_7 - A_0 = 000FFH. Unlocked: DQ_3 = 1 / Locked: DQ_3 = 0.

For GLS36VF1602E,

Greenliant ID is read with A₃ = 0 (Address range = C0000H to C0007H),

User ID is read with $A_3 = 1$ (Address range = $\tilde{C}0010H$ to C0017H).

Lock Status is read with A7-A0 = C00FFH. Unlocked: DQ3 = 1 / Locked: DQ3 = 0.

6. SIWA = User Security ID Program word/byte address

For GLS36VF1601E, valid Word-Addresses for User Sec ID are from 00010H-00017H.

For GLS36VF1602E, valid Word-Addresses for User Sec ID are from C0010H-C0017H.

All 4 cycles of User Security ID Program and Program Lock-out must be completed before going back to Read-Array mode.

- 7. The User Security ID Program Lock-out command must be executed in x16 mode (BYTE#=VIH).
- The device does not remain in Software Product Identification mode if powered down.
- 9. A₁₉ and A₁₈ = BK_X (Bank Address): address of the bank that is switched to Software ID/CFI Mode

With A_{17} - A_1 = 0; Greenliant Manufacturer's ID = 00BFH, is read with A_0 = 0

GLS36VF1601E Device ID = 734BH, is read with $A_0 = 1$

GLS36VF1602E Device ID = 734AH, is read with A₀ = 1

- 10. Both Software ID Exit operations are equivalent
- 11. If users never lock after programming, User Sec ID can be programmed over the previously unprogrammed bits (data=1) using the User Sec ID mode again (the programmed "0" bits cannot be reversed to "1").

For GLS36VF1601E, valid Word-Addresses for User Sec ID are from 00010H-00017H.

For GLS36VF1602E, valid Word-Addresses for User Sec ID are from C0010H-C0017H.



Data Sheet

TABLE 7: CFI Query Identification String¹

Address	Address		
x16 Mode	x8 Mode	Data ²	Description
10H	20H	0051H	Query Unique ASCII string "QRY"
11H	22H	0052H	
12H	24H	0059H	
13H	26H	0001H	Primary OEM command set
14H	28H	0007H	
15H	2AH	0000H	Address for Primary Extended Table
16H	2CH	0000H	
17H	2EH	0000H	Alternate OEM command set (00H = none exists)
18H	30H	0000H	
19H	32H	0000H	Address for Alternate OEM extended Table (00H = none exits)
1AH	34H	0000H	

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TABLE 8: System Interface Information

Address x16 Mode	Address x8 Mode	Data ¹	Description
1BH	36H	0027H	V _{DD} Min (Program/Erase)
			DQ ₇ -DQ ₄ : Volts, DQ ₃ -DQ ₀ : 100 millivolts
1CH	38H	0036H	V _{DD} Max (Program/Erase) DQ ₇ -DQ ₄ : Volts, DQ ₃ -DQ ₀ : 100 millivolts
1DH	3AH	0000H	V_{PP} min (00H = no V_{PP} pin)
1EH	3CH	0000H	V_{PP} max (00H = no V_{PP} pin)
1FH	3EH	0004H	Typical time out for Program 2^{N} µs (2^{4} = 16 µs)
20H	40H	0000H	Typical time out for min size buffer program 2 ^N μs (00H = not supported)
21H	42H	0004H	Typical time out for individual Sector/Block-Erase 2 ^N ms (2 ⁴ = 16 ms)
22H	44H	0006H	Typical time out for Chip-Erase 2 ^N ms (2 ⁶ = 64 ms)
23H	46H	0001H	Maximum time out for Program 2^N times typical $(2^1 \times 2^4 = 32 \mu s)$
24H	48H	0000H	Maximum time out for buffer program 2 ^N times typical
25H	4AH	0001H	Maximum time out for individual Sector-/Block-Erase 2 ^N times typical (2 ¹ x 2 ⁴ = 32 ms)
26H	4CH	0001H	Maximum time out for Chip-Erase 2 ^N times typical (2 ¹ x 2 ⁶ = 128 ms)

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1. In x8 mode, only the lower byte of data is output.

^{1.} Refer to CFI publication 100 for more details.

^{2.} In x8 mode, only the lower byte of data is output.



Data Sheet

TABLE 9: Device Geometry Information

Address x16 Mode	Address x8 Mode	Data ¹	Description
27H	4EH	0015H	Device size = 2^{N} Bytes (15H = 21; 2^{21} = 2 MByte)
28H	50H	0002H	Flash Device Interface description; 0002H = x8/x16 asynchronous interface
29H	52H	0000H	
2AH	54H	0000H	Maximum number of bytes in multi-byte write = 2 ^N (00H = not supported)
2BH	56H	0000H	
2CH	58H	0002H	Number of Erase Sector/Block sizes supported by device
2DH	5AH	00FFH	Sector Information (y + 1 = Number of sectors; z x 256B = sector size)
2EH	5CH	0001H	y = 511 + 1 = 512 sectors (01FFH = 512)
2FH	5EH	0010H	
30H	60H	0000H	z = 16 x 256 Bytes = 4 KByte/sector (0010H = 16)
31H	62H	001FH	Block Information (y + 1 = Number of blocks; z x 256B = block size)
32H	64H	0000H	y = 31 + 1 = 32 blocks (001FH = 31)
33H	66H	0000H	
34H	68H	0001H	z = 256 x 256 Bytes = 64 KByte/block (0100H = 256)

^{1.} In x8 mode, only the lower byte of data is output.

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Data Sheet

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under "Absolute Maximum Stress Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Temperature Under Bias	55°C to +125°C
Storage Temperature	65°C to +150°C
D. C. Voltage on Any Pin to Ground Potential	0.5V to V _{DD} +0.5V
Transient Voltage (<20 ns) on Any Pin to Ground Potential	2.0V to V _{DD} +2.0V
Package Power Dissipation Capability (T _A = 25°C)	
Surface Mount Solder Reflow Temperature	260°C for 10 seconds
Output Short Circuit Current	

Operating Range:

Range	Ambient Temp	V_{DD}
Commercial	0°C to +70°C	2.7-3.6V
Industrial	-40°C to +85°C	2.7-3.6V

AC Conditions of Test

Input Rise/Fall Time 5 ns
Output Load
See Figures 22 and 23



Data Sheet

TABLE 10: DC Operating Characteristics V_{DD} = 2.7-3.6V

				Limits		
Symbol	Parameter	Freq	Min	Max	Units	Test Conditions
I_{DD}^{1}	Active V _{DD} Current					
	Read	5 MHz		15	mA	CE#=V _{IL} WE#=OE#=V _{IH}
		1 MHz		4	mA	CE#-VIL, VVE#-OE#-VIH
	Program and Erase			30	mA	CE#=WE#=V _{IL} , OE#=V _{IH}
	Concurrent Read/Write	5 MHz		45	mA	CE#=V _{IL} OE#=V _{IH}
		1 MHz		35	mA	GL#-VIL, GL#-VIH
I _{SB}	Standby V _{DD} Current			20	μΑ	CE#, RST#=V _{DD} ±0.3V
I _{ALP}	Auto Low Power V _{DD} Current			20	μΑ	CE#=0.1V, V_{DD} = V_{DD} Max WE#= V_{DD} -0.1V Address inputs=0.1V or V_{DD} -0.1V
I _{RT}	Reset V _{DD} Current			20	μΑ	RST#=GND
ILI	Input Leakage Current			1	μΑ	V_{IN} =GND to V_{DD} , V_{DD} = V_{DD} Max
I _{LIW}	Input Leakage Current on WP# pin and RST# pin			10	μΑ	WP#=GND to V_{DD} , V_{DD} = V_{DD} Max RST#=GND to V_{DD} , V_{DD} = V_{DD} Max
I _{LO}	Output Leakage Current			1	μΑ	V _{OUT} =GND to V _{DD} , V _{DD} =V _{DD} Max
V _{IL}	Input Low Voltage			0.8	V	V _{DD} =V _{DD} Min
V _{ILC}	Input Low Voltage (CMOS)			0.3	V	V _{DD} =V _{DD} Max
V _{IH}	Input High Voltage		$0.7\ V_{DD}$	V _{DD} +0.3	V	V _{DD} =V _{DD} Max
V _{IHC}	Input High Voltage (CMOS)		V_{DD} -0.3	V _{DD} +0.3	V	V _{DD} =V _{DD} Max
V _{OL}	Output Low Voltage			0.2	V	I _{OL} =100 μA, V _{DD} =V _{DD} Min
V _{OH}	Output High Voltage		V _{DD} -0.2		V	I _{OH} =-100 μA, V _{DD} =V _{DD} Min

^{1.} Address input = V_{ILT}/V_{IHT}, V_{DD}=V_{DD} Max (See Figure 22)

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TABLE 11: Recommended System Power-up Timings

Symbol	Parameter	Minimum	Units
T _{PU-READ} ¹	Power-up to Read Operation	100	μs
T _{PU-WRITE} ¹	Power-up to Write Operation	100	μs

T11.0 1274 1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 12: Capacitance (T_A = 25°C, f=1 Mhz, other pins open)

Parameter	Description	Test Condition	Maximum
C _{I/O} ¹	I/O Pin Capacitance	V _{I/O} = 0V	10 pF
C _{IN} ¹	Input Capacitance	$V_{IN} = 0V$	10 pF

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TABLE 13: Reliability Characteristics

Symbol	Parameter	Minimum Specification	Units	Test Method
N _{END} ¹	Endurance	10,000	Cycles	JEDEC Standard A117
T _{DR} ¹	Data Retention	100	Years	JEDEC Standard A103
I _{LTH} ¹	Latch Up	100 + I _{DD}	mA	JEDEC Standard 78

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^{1.} This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

^{1.} This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.



Data Sheet

AC CHARACTERISTICS

TABLE 14: Read Cycle Timing Parameters V_{DD} = 2.7-3.6V

Symbol	Parameter	Min	Max	Units
T _{RC}	Read Cycle Time	70		ns
T _{CE}	Chip Enable Access Time		70	ns
T _{AA}	Address Access Time		70	ns
T _{OE}	Output Enable Access Time		30	ns
T _{CLZ} ¹	CE# Low to Active Output	0		ns
T _{OLZ} ¹	OE# Low to Active Output	0		ns
T _{CHZ} ¹	CE# High to High-Z Output		16	ns
T _{OHZ} ¹	OE# High to High-Z Output		16	ns
T _{OH} ¹	Output Hold from Address Change	0		ns
T _{RP} ¹	RST# Pulse Width	500		ns
T _{RHR} ¹	RST# High before Read	50		ns
T _{RY} ^{1,2}	RST# Pin Low to Read Mode		20	μs

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TABLE 15: Program/Erase Cycle Timing Parameters

Symbol	Parameter	Min	Max	Units
T _{BP}	Program Time		10	μs
T _{AS}	Address Setup Time	0		ns
T _{AH}	Address Hold Time	40		ns
T _{CS}	WE# and CE# Setup Time	0		ns
T _{CH}	WE# and CE# Hold Time	0		ns
T _{OES}	OE# High Setup Time	0		ns
T _{OEH}	OE# High Hold Time	10		ns
T _{CP}	CE# Pulse Width	40		ns
T _{WP}	WE# Pulse Width	40		ns
T _{WPH} ¹	WE# Pulse Width High	30		ns
T _{CPH} ¹	CE# Pulse Width High	30		ns
T _{DS}	Data Setup Time	30		ns
T _{DH} ¹	Data Hold Time	0		ns
T _{IDA} 1	Software ID Access and Exit Time		150	ns
T _{SE}	Sector-Erase		25	ms
T _{BE}	Block-Erase		25	ms
T _{SCE}	Chip-Erase		50	ms
T _{ES}	Erase-Suspend Latency		10	μs
T _{BY} ^{1,2}	RY/BY# Delay Time		90	ns
T _{BR} ¹	Bus Recovery Time		0	μs

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^{1.} This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

^{2.} This parameter applies to Sector-Erase, Block-Erase, and Program operations. This parameter does not apply to Chip-Erase operations.

^{1.} This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.



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2. This parameter applies to Sector-Erase, Block-Erase, and Program operations. This parameter does not apply to Chip-Erase operations.

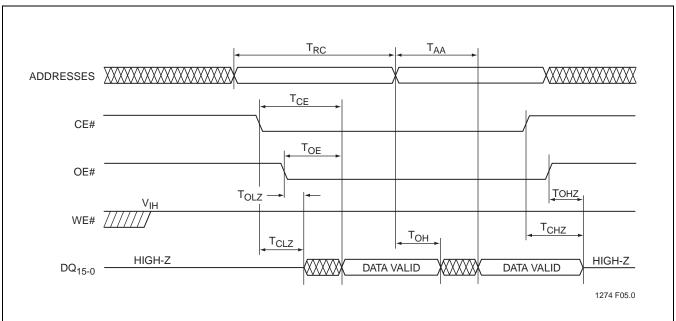


FIGURE 8: Read Cycle Timing Diagram



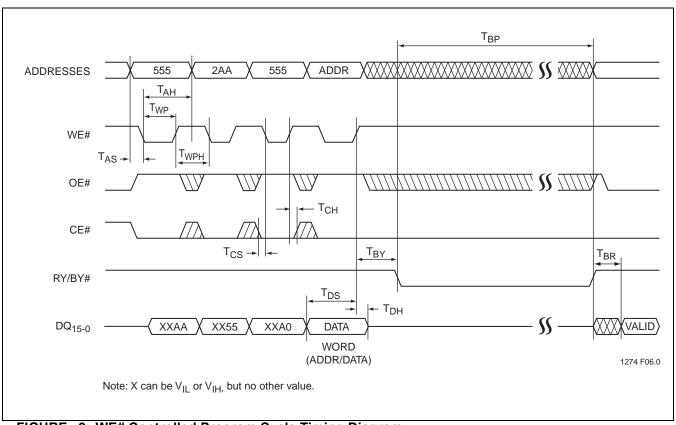


FIGURE 9: WE# Controlled Program Cycle Timing Diagram

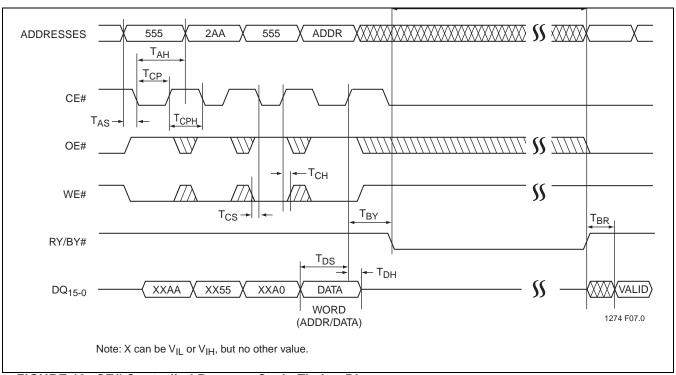


FIGURE 10: CE# Controlled Program Cycle Timing Diagram

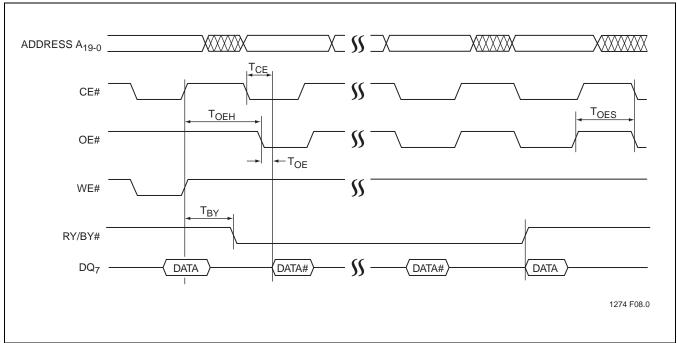


FIGURE 11: Data# Polling Timing Diagram



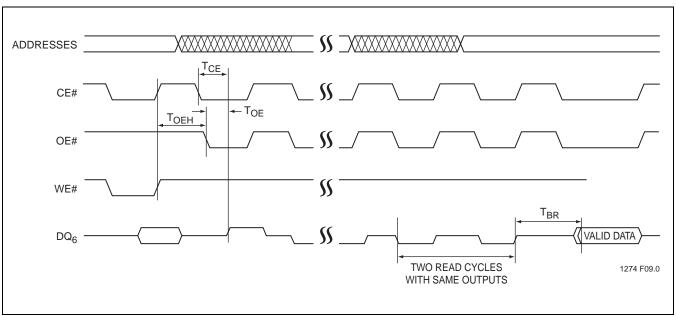


FIGURE 12: Toggle Bit Timing Diagram

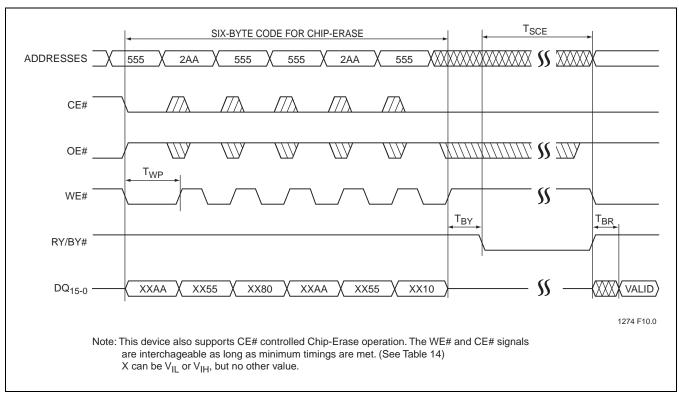


FIGURE 13: WE# Controlled Chip-Erase Timing Diagram

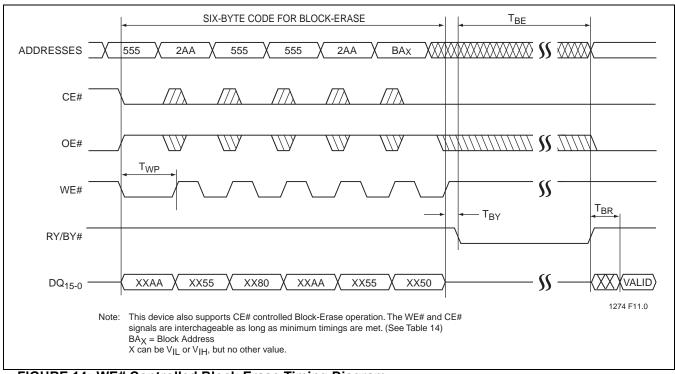


FIGURE 14: WE# Controlled Block-Erase Timing Diagram

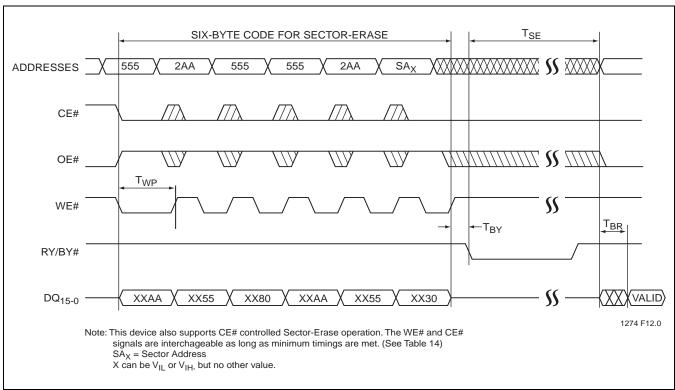


FIGURE 15: WE# Controlled Sector-Erase Timing Diagram



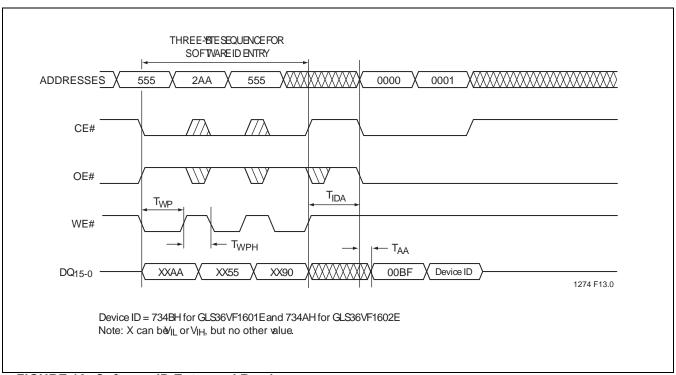


FIGURE 16: Software ID Entry and Read

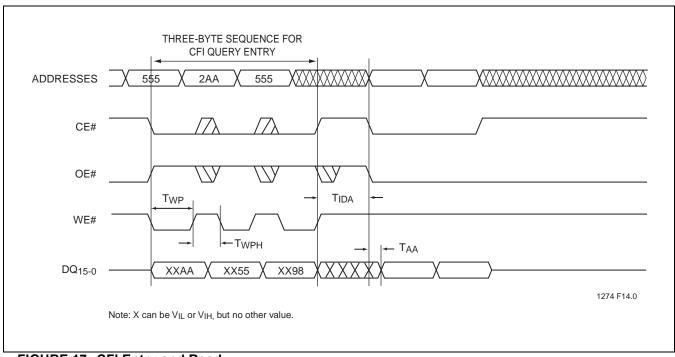


FIGURE 17: CFI Entry and Read

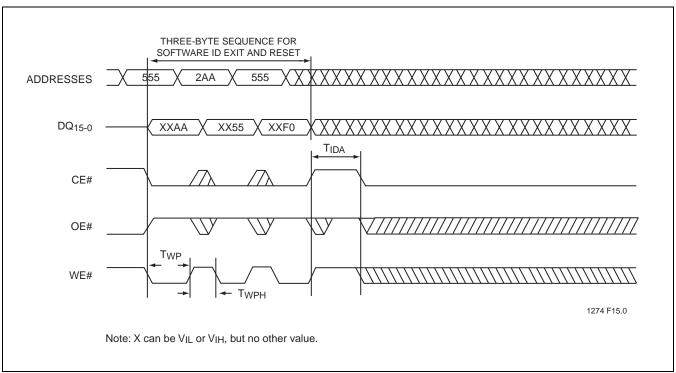


FIGURE 18: Software ID Exit/CFI Exit

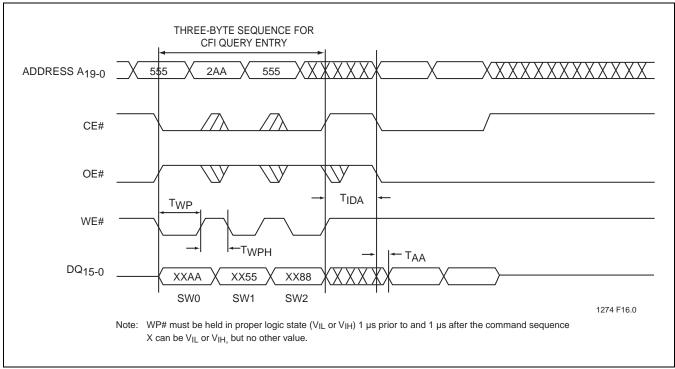


FIGURE 19: Sec ID Entry



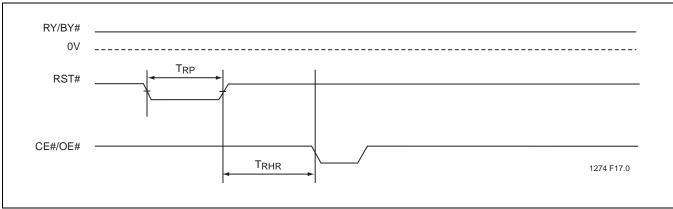


FIGURE 20: RST# Timing Diagram (When no internal operation is in progress)

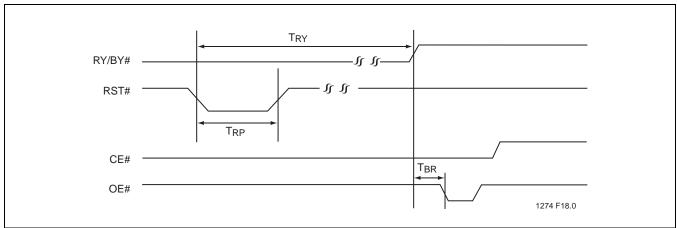
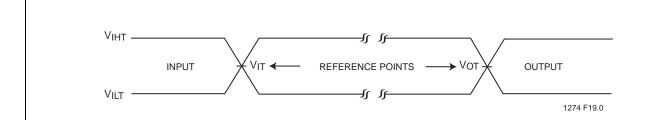


FIGURE 21: RST# Timing Diagram (During Sector- or Block-Erase operation)



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AC test inputs are driven at V_{IHT} (0.9 V_{DD}) for a logic "1" and V_{ILT} (0.1 V_{DD}) for a logic "0". Measurement reference points for inputs and outputs are V_{IT} (0.5 V_{DD}) and V_{OT} (0.5 V_{DD}). Input rise and fall times (10% \leftrightarrow 90%) are <5 ns.

> Note: V_{IT} - V_{INPUT} Test Vor - Vourput Test V_{IHT} - V_{INPUT} HIGH Test V_{ILT} - V_{INPUT} LOW Test

FIGURE 22: AC Input/Output Reference Waveforms

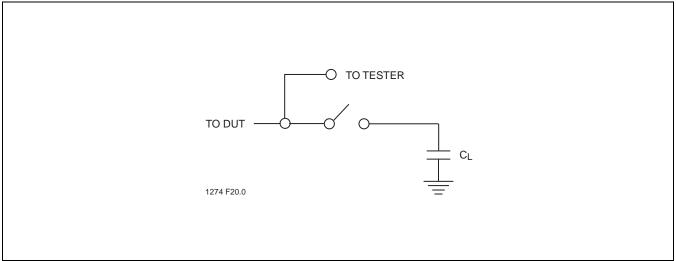


FIGURE 23: A Test Load Example



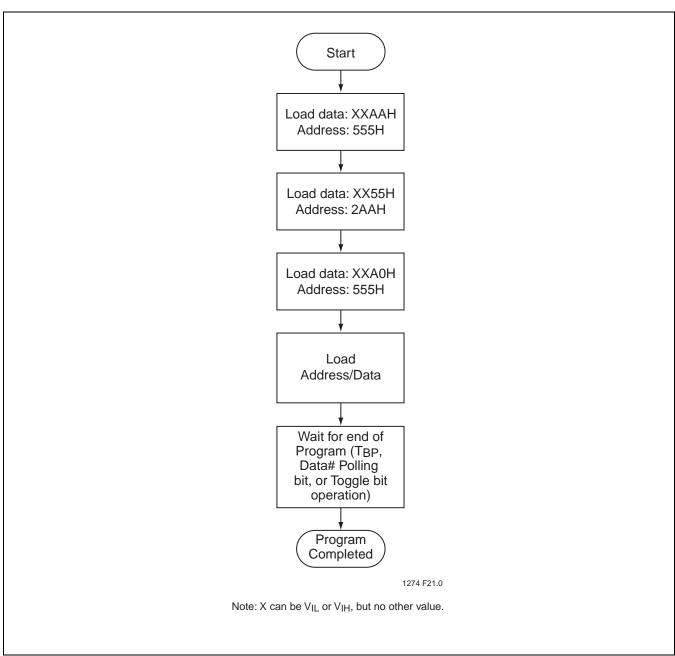


FIGURE 24: Program Algorithm

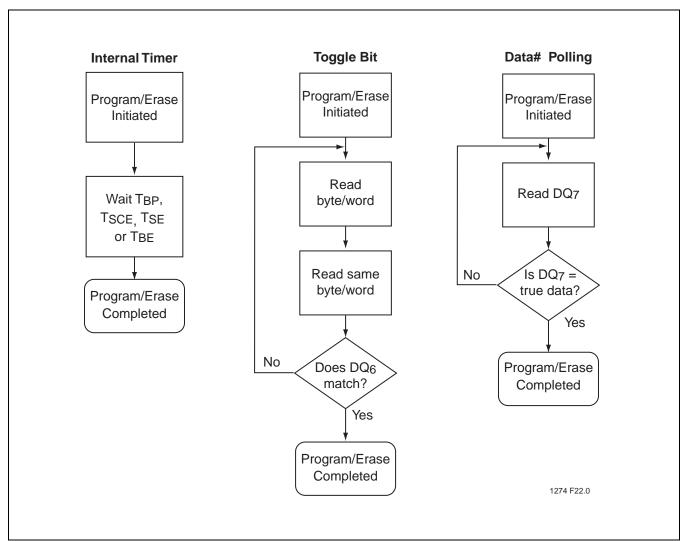


FIGURE 25: Wait Options



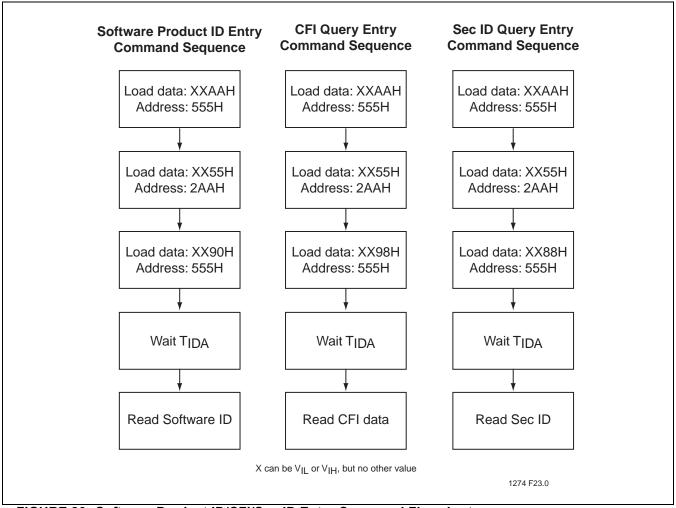


FIGURE 26: Software Product ID/CFI/Sec ID Entry Command Flowcharts

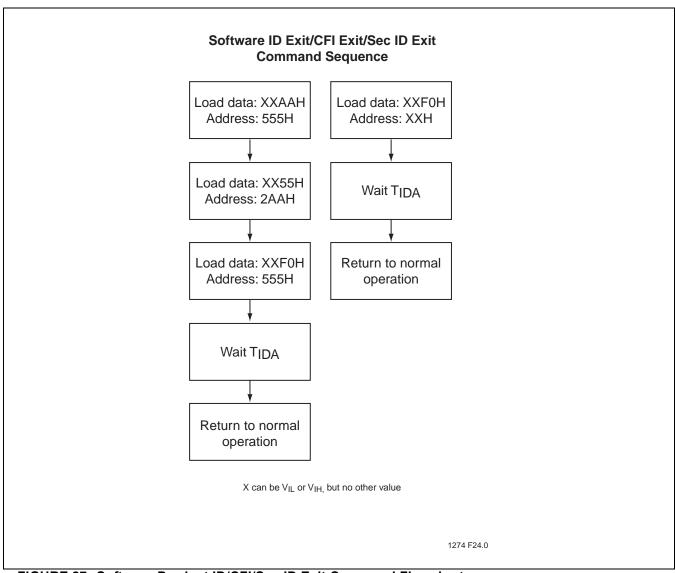


FIGURE 27: Software Product ID/CFI/Sec ID Exit Command Flowcharts



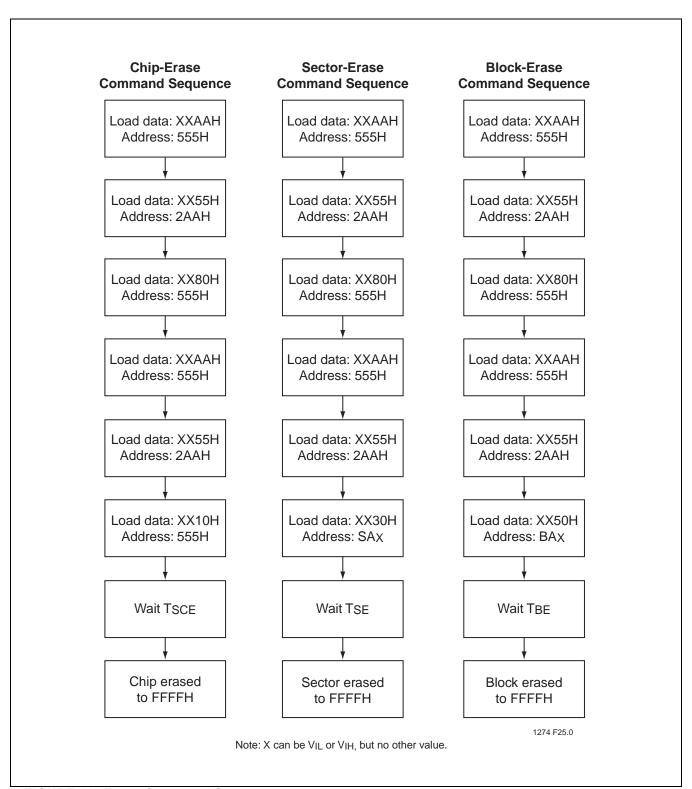
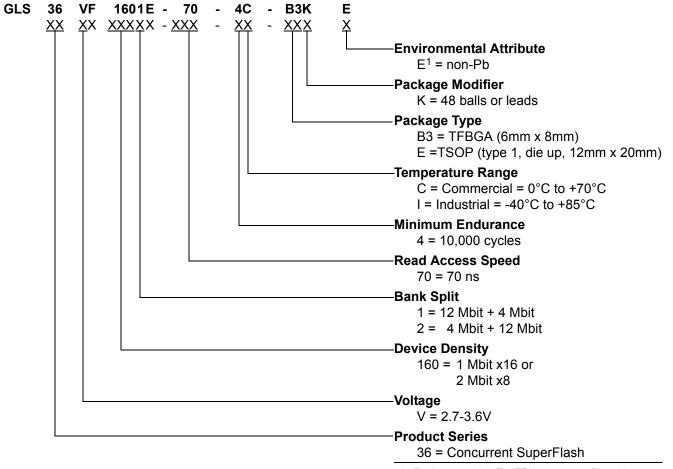


FIGURE 28: Erase Command Sequence



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PRODUCT ORDERING INFORMATION



Environmental suffix "E" denotes non-Pb solder. Greenliant non-Pb solder devices are "RoHS Compliant".

Valid combinations for GLS36VF1601E

GLS36VF1601E-70-4C-B3KE GLS36VF1601E-70-4C-EKE GLS36VF1601E-70-4I-B3KE GLS36VF1601E-70-4I-EKE

Valid combinations for GLS36VF1602E

GLS36VF1602E-70-4C-B3KE GLS36VF1602E-70-4C-EKE GLS36VF1602E-70-4I-B3KE GLS36VF1602E-70-4I-EKE

Note: Valid combinations are those products in mass production or will be in mass production. Consult your Greenliant sales representative to confirm availability of valid combinations and to determine availability of new combinations.



PACKAGING DIAGRAMS

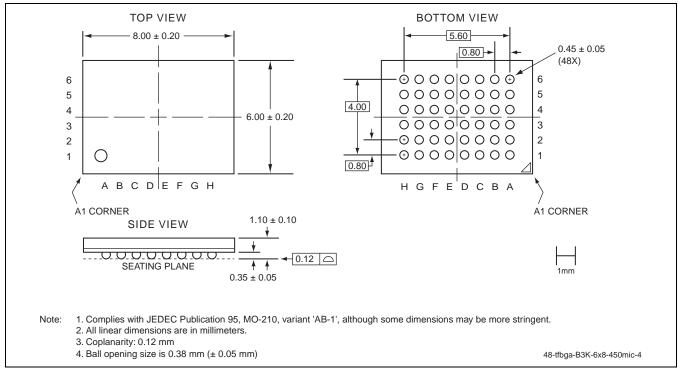


FIGURE 29: 48-ball Thin-profile, Fine-pitch Ball Grid Array (TFBGA) 6mm x 8mm Greenliant Package Code: B3K

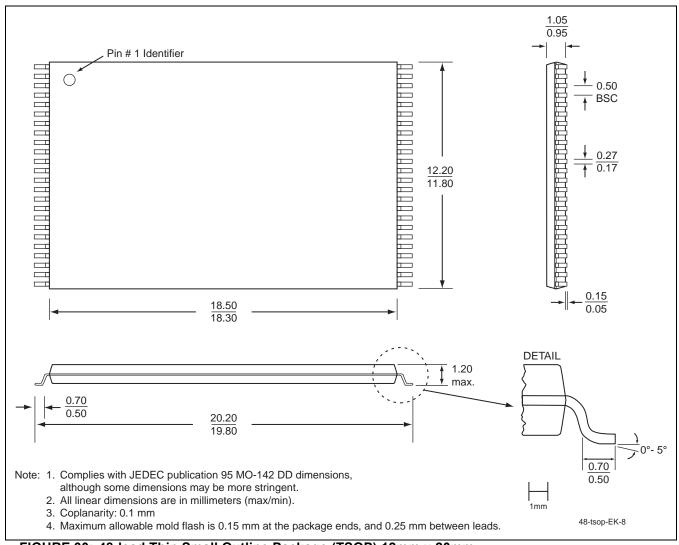


FIGURE 30: 48-lead Thin Small Outline Package (TSOP) 12mm x 20mm **Greenliant Package Code: EK**



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TABLE 16: Revision History

Numbe	-	
r	Description	Date
00	Initial release of data sheet	Oct 2004
01	• Updates to data sheet Tables 1, 4, 5, 8, 9, and 13. Added RoHS compliance information on page 1 and in the "Product Ordering Information" on page 34	Mar 2005
	Updated sector information in Table 9, "Device Geometry Information" on page 16	
	Updated Active Current values and test conditions in Table 10 on page 18	
	Updated OE timings in Table 14 on page 19	
	Added a Reset footnote to Table 5 on page 13	
	Updated the footnote for Table 2 on page 5	
	Corrected the Address Format in footnote 1 in Table 6 on page 14	
	 Clarified the solder temperature profile under "Absolute Maximum Stress Ratings" on page 17 	
02	Updated "Erase-Suspend/Erase-Resume Operations" on page 4	Jul 2005
	• Updated T _{ES} parameter from 20 μs to 10 μs in Table 15 on page 19	
03	Made changes to support Pb-free packages only	Nov 2005
04	Edited Tby TY/BY# Delay Time in Table 15 on page 19 from 90ns Min to 90ns Max	Nov 2009
05	Transferred from SST to Greenliant	May 2010

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